



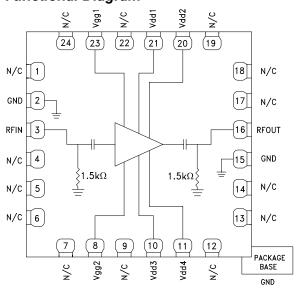
GaAs pHEMT MMIC 2 WATT POWER AMPLIFIER, 5.5 - 8.5 GHz

Typical Applications

The HMC7357LP5GE is ideal for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios
- VSAT & SATCOM

Functional Diagram



Features

+35 dBm Pout @ 34% PAE

High P1dB Output Power: +34 dBm

High Output IP3: +41.5 dBm

High Gain: 29 dB

50 Ohm Matched Input/Output

Supply Voltage: Vdd = +8V @ 1200 mA

24-Lead 5x5 mm SMT Package

General Description

The HMC7357LP5GE is a three-stage GaAs pHEMT MMIC Medium Power Amplifier that operates between 5.5 and 8.5 GHz. The amplifier provides 29 dB of gain and +35 dBm of saturated output power at 34% PAE from a +8V supply. With an excellent Output IP3 of +41.5 dBm, the HMC7357LP5GE is ideal for linear applications such as high capacity point-to-point and point-to-multi-point radios or VSAT/SATCOM applications demanding +35 dBm of efficient saturated output power. The RF I/Os are internally matched to 50 Ohms for ease of use. The HMC7357LP5GE is packaged in a leadless 5x5 mm plastic surface mount package and is compatible with surface mount manufacturing techniques.

Electrical Specifications, $T_A = +25^{\circ}$ C Vdd1 = Vdd2 = Vdd3 = Vdd4 = 8V, Idd = 1200 mA [1]

| Parameter | Min. | Тур. | Max. | Min. | Тур. | Max. | Units |
|---|---------|--------|---------|------|--------|------|--------|
| Frequency Range | 5.5 - 7 | | 7 - 8.5 | | | GHz | |
| Gain | 26.5 | 29.5 | | 28 | 31 | | dB |
| Gain Variation Over Temperature | | 0.0214 | | | 0.0234 | | dB/ °C |
| Input Return Loss | | 14 | | | 14 | | dB |
| Output Return Loss | | 22 | | | 15 | | dB |
| Output Power for 1 dB Compression (P1dB) | 31.5 | 34.5 | | 31.5 | 34.5 | | dBm |
| Saturated Output Power (Psat) | | 35 | | | 35 | | dBm |
| Output Third Order Intercept (IP3) ^[2] | | 41.5 | | | 41.5 | | dBm |
| Total Supply Current (Idd) | | 1200 | | | 1200 | | mA |

^[1] Adjust Vgg between -2 to -0.4V to achieve Idd = 1200 mA typical.

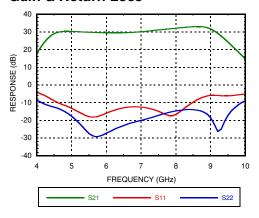
^[2] Measurement taken at +8V @ 1200 mA, Pout / Tone = +20 dBm



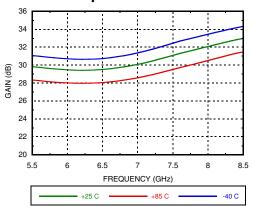


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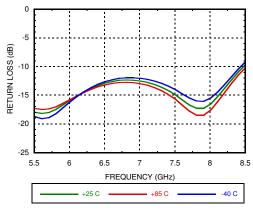
Gain & Return Loss



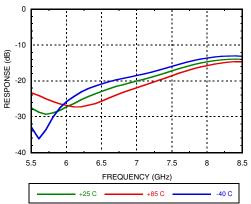
Gain vs. Temperature



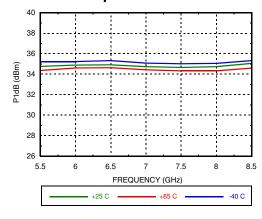
Input Return Loss vs. Temperature



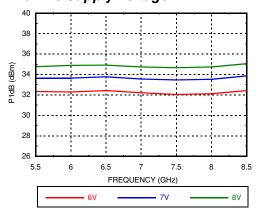
Output Return Loss vs. Temperature



P1dB vs. Temperature



P1dB vs Supply Voltage

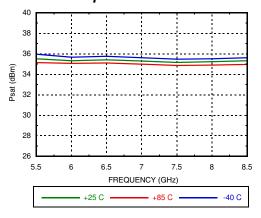




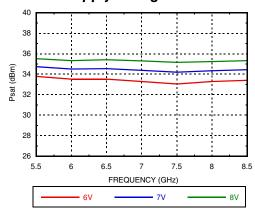


GaAs pHEMT MMIC 2 WATT POWER AMPLIFIER, 5.5 - 8.5 GHz

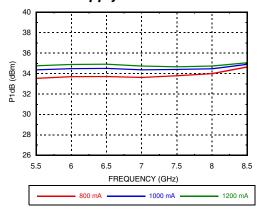
Psat vs. Temperature



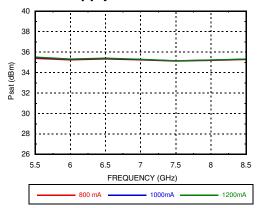
Psat vs. Supply Voltage



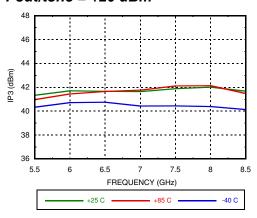
P1dB vs. Supply Current



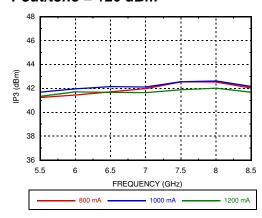
Psat vs. Supply Current



Output IP3 vs. Temperature, Pout/tone = +20 dBm



Output IP3 vs. Supply Current, Pout/tone = +20 dBm



GaAs pHEMT MMIC 2 WATT

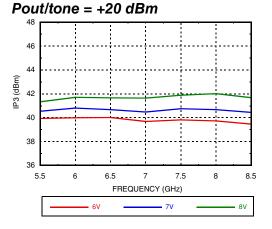
POWER AMPLIFIER, 5.5 - 8.5 GHz



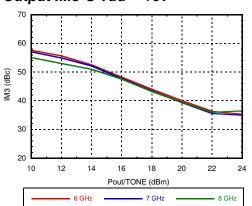
v00.0813



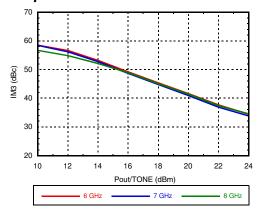
Output IP3 vs. Supply Voltage,



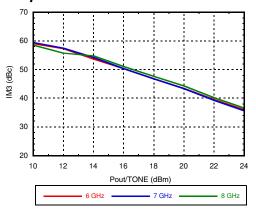
Output IM3 @ Vdd = +6V



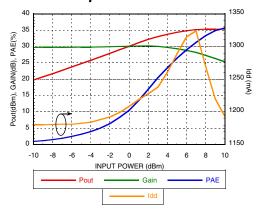
Output IM3 @ Vdd =+7V



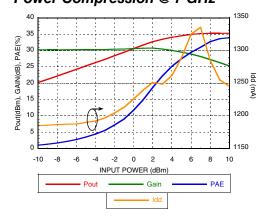
Output IM3 @ Vdd = +8V



Power Compression @ 6 GHz



Power Compression @ 7 GHz

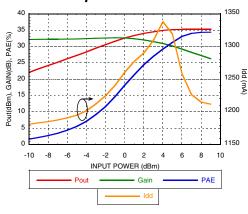




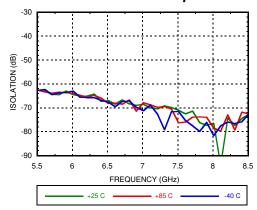


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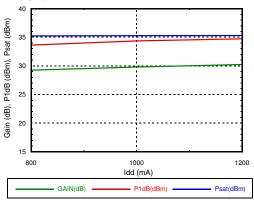
Power Compression @ 8 GHz



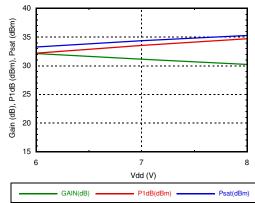
Reverse Isolation vs. Temperature



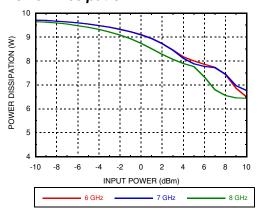
Gain & Power vs. Supply Current @ 7 GHz



Gain & Power vs. Supply Voltage @ 7 GHz



Power Dissipation







GaAs pHEMT MMIC 2 WATT **POWER AMPLIFIER, 5.5 - 8.5 GHz**

Absolute Maximum Ratings

| Drain Bias Voltage (Vdd) | +9 Vdc | | |
|--|-----------------------|--|--|
| Gate Bias Voltage (Vgg) | -2 to -0.4 Vdc | | |
| RF Input Power (RFIN) | +22 dBm | | |
| Channel Temperature | 175 °C | | |
| Continuous Pdiss (T= 85 °C) (derate 133mW/°C above 85 °C) | 12.6 W | | |
| Thermal Resistance (channel to ground paddle) | 7.5 °C/W | | |
| Storage Temperature | -65 to 150°C | | |
| Operating Temperature | -40 to 85 °C | | |
| ESD Sensitivity (HBM) | Class 1A, passed 250V | | |

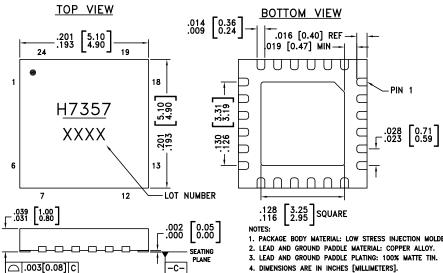
Typical Supply Current vs. Vdd

| Vdd (V) | Idd (mA) | | |
|---------|----------|--|--|
| +6 | 1200 | | |
| +7 | 1200 | | |
| +8 | 1200 | | |

Adjust Vgg to achieve Idd = 1200 mA



Outline Drawing



- 1. PACKAGE BODY MATERIAL: LOW STRESS INJECTION MOLDED PLASTIC SILICA AND SILICON IMPREGNATED.
- DIMENSIONS ARE IN INCHES [MILLIMETERS].
- 5. LEAD SPACING TOLERANCE IS NON-CUMULATIVE.
- 6. CHARACTERS TO BE HELVETICA MEDIUM, .025 HIGH, WHITE INK, OR LASER MARK LOCATED APPROX. AS SHOWN.
- PAD BURR LENGTH SHALL BE 0.15mm MAX. PAD BURR HEIGHT SHALL BE 0.25mm MAX.
- 8. PACKAGE WARP SHALL NOT EXCEED 0.05mm
- 9. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
- 10. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED PCB LAND PATTERN.

Package Information

| Part Number | Package Body Material | Lead Finish | MSL Rating [2] | Package Marking [1] | |
|--------------|--|---------------|----------------|----------------------|--|
| HMC7357LP5GE | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL1 | <u>H7357</u> XXXX | |

^{[1] 4-}Digit lot number XXXX

^[2] Max peak reflow temperature of 260 °C





GaAs pHEMT MMIC 2 WATT POWER AMPLIFIER, 5.5 - 8.5 GHz

Pin Descriptions

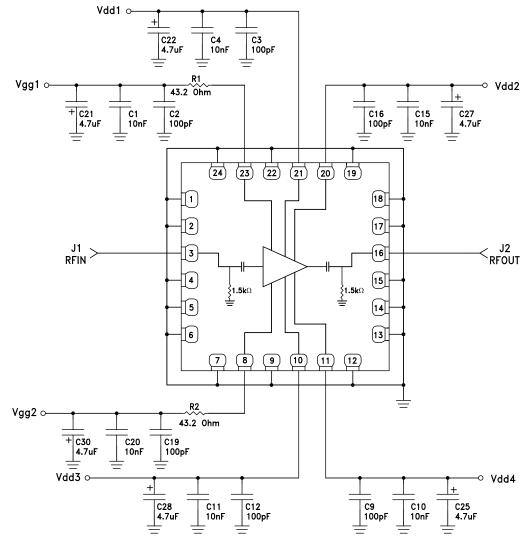
| Pad Number | Function | Description | Interface Schematic |
|--|---------------------------|--|---|
| 1, 4, 5, 6, 7, 9, 12, 13, 14, 17, 18, 19, 22, 24 | N/C | These pins are not connected internally; however all data shown herein was measured with these pins connected to RF/DC ground externally. | |
| 2, 15 | GND | These pins and exposed ground paddle must be connected to RF/DC ground. | GND = |
| 3 | RFIN | This pin is DC coupled and matched to 50 Ohms. | RFINΟ |
| 8, 23 | Vgg2, Vgg1 | Gate control for PA. Adjust Vgg to achieve recommended bias current. External bypass capacitors of 100 pF, 10 nF, and 4.7 μF are required. Apply Vgg bias to either pin 8 or pin 23. | Vgg1,2 0 |
| 10, 11, 20, 21 | Vdd3, Vdd4, Vdd2, Vdd1 | Drain bias voltage for the amplifier. External bypass capacitors of 100 pF, 10 nF, and 4.7 μF are required. | ○Vdd1−4 |
| 16 | RFOUT | This pin is DC coupled and matched to 50 Ohms. | $ \begin{array}{c c} \hline \\ \uparrow \\ \hline \\ 1.5k\Omega \end{array} $ |





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Application Circuit

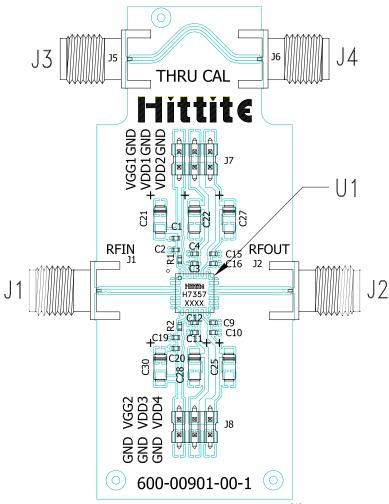






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Evaluation PCB



List of Materials for Evaluation PCB EV1HMC7357LP5 [1]

| Item | Description |
|------------------------------|-------------------------------|
| J1 - J4 | "K" Connector, SRI |
| J7, J8 | DC Pin |
| C2, C3, C9, C12, C16, C19 | 100 pF Capacitor, 0402 Pkg. |
| C1, C4, C10, C11, C15, C20 | 10000 pF Capacitor, 0402 Pkg. |
| C21, C22, C25, C27, C28, C30 | 4.7 uF Capacitor, Case A Pkg. |
| R1, R2 | 43.2 Ohm Resistor, 0402 Pkg |
| U1 | HMC7357LP5GE Amplifier |
| PCB [2] | 600-00901-00 Eval Board |

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.







ANALOGDEVICES

GaAs pHEMT MMIC 2 WATT POWER AMPLIFIER, 5.5 - 8.5 GHz

Notes: